

## **INCHANGE SEMICONDUCTOR**

# iscN-Channel MOSFET Transistor

# TK3A65D, ITK3A65D

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# • FEATURES

- Low drain-source on-resistance: RDs(ON) = 1.93Ω (typ.)
- · Enhancement mode:

Vth = 2.4 to 4.4V (VDs = 10 V, ID=1.0mA)

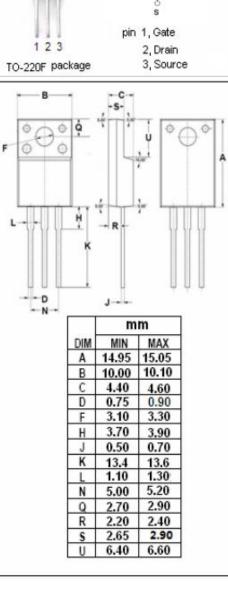
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## DESCRITION

Switching Voltage Regulators

#### • ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)

SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>DSS</sub>	Drain-Source Voltage	650	V				
V <sub>GS</sub>	Gate-Source Voltage	±30	V				
ID	Drain Current-Continuous	3	А				
I <sub>DM</sub>	Drain Current-Single Pulsed	12	А				
P <sub>D</sub>	Total Dissipation @Tc=25°C	35	W				
Tj	Max. Operating Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature	-55~150	°C				



#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	3.57	°C <b>/W</b>
Rth(ch-a)	Rth(ch-a) Channel-to-ambient thermal resistance		°C <b>/W</b>

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### **ELECTRICAL CHARACTERISTICS**

 $T_c=25^{\circ}C$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> = 10mA	650			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = 10V; I <sub>D</sub> =1.0mA	2.4		4.4	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =1.5A		1930	2250	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V			±1	μA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =650V; V <sub>GS</sub> = 0V			10	μA
VSDF	Diode forward voltage	I <sub>DR</sub> =3A, V <sub>GS</sub> = 0 V			1.7	V

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